Q.P. Code: 19EE0240

Reg. No:

SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY: PUTTUR

R19

Max. Marks: 60

10M

2M

8M

(AUTONOMOUS)

B. TECH II Year I Semester Regular Examinations Feb-2021 BASIC ELECTRICAL & ELECTRONICS ENGINEERING

(Mechanical Engineering)

Time: 3 hours

(Answer all Six Units $6 \times 10 = 60$ Marks)



Q.1 Three resistances of values 20, 30 and 50 are connected in series across 20 V DC supply.
 10M Calculate, i) Equivalent resistance of the circuit. ii) Total current from the supply.iii) Voltage drop across each resistor. iv) Power dissipated in each resistor.



Q.2 Find the current delivered by the source for the circuit shown in figure.

20 Ω 30 Ω 5 Ω 20 Ω 30 Ω 5 Ω 5 Ω 220 V UNIT-II

Q.3 a State Thevenin's theorem.

b Find the Thevenin's equivalent circuit across AB for the circuit shown.

 $\begin{array}{c}
3 \Omega \\
50 V \\
4 \Omega \\
B
\end{array}$

OR

Q.4 a The given ABCD parameters are A=2, B=0.9, C=1.2, D=0.5. Find Y-parameters.
b The given Y-parameters are Y11=0.5, Y12=Y21=0.6, Y22=0.9. Find the impedance 5M parameters.

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UNIT	-III
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- Derive Torque equation of dc motor. 0.5 а
 - The counter emf of Shunt motor is 227 V. The field resistance is 160Ω and field current b **5M** 1.5A. If the line current is 36.5A, find the armature resistance also find armature current when the motor is stationary.

OR

Explain constructional details of transformer. Q.6 **5M** a A 20 kVA, 2000/200 V, 50 Hz transformer has 66 secondary turns. Calculate the number b **5M** of primary turns and primary and secondary currents. Neglect losses.



Q.7 Describe the working of a PN junction diode when it is connected in forward bias and reverse 10M bias. Draw VI Characteristics of PN Junction Diode.

OR

- With neat diagram, explain the working principle of Half Wave Rectifier. Draw its input **5M Q.8** a and output waveforms.
 - Derive the expression for Ripple factor and Efficiency of Half Wave Rectifier. b **5M**

		UNIT-II	
Q.9	а	Discuss with neat diagrams of the Common Emitter Configuration.	5M
	b	Draw the characteristics of CE configuration and explain it.	5M
		OR	
Q.10	a	Derive the relationship between I_C , I_B , I_E of BJT configuration.	5 M
	b	A transistor operating in CB configuration has $I_{C} = 2.98$ mA, $I_{E} = 3.00$ mA and $I_{CO} = 0.01$	5M
		mA. What current will flow in the collector circuit for this transistor when connected in	
		CE configuration with a base current of 30µA?	
		The same interaction is a second second different strength of the second second second second second second second	
		UNIT-III	

Q.11	а	Explain the Drain characteristics of JFET.	5M
	b	Explain the transfer characteristics of JFET.	5 M
		OR	
Q.12	а	Draw the construction of Enhancement type MOSFET and explain its operation.	5M
	b	Explain the operation of Depletion type MOSFET	5M

*** END ***

5M